

# INK0103AC1

High speed switching  
Silicon N-channel MOSFET

## DESCRIPTION

INK0103AC1 is a Silicon N-channel MOSFET.

This product is most suitable for low voltage use such as portable machinery, because of low voltage drive and low resistance.

## FEATURE

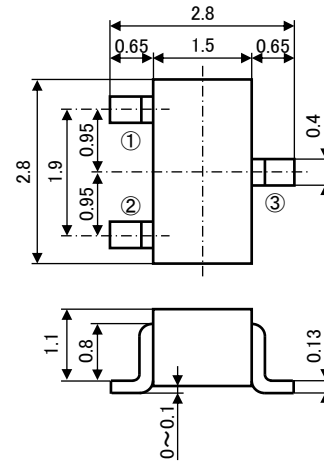
- Input impedance is high, and not necessary to consider a drive electric current.
- Drive voltage 1.8V
- Low on Resistance.
  - $R_{DS(ON)}=0.33\ \Omega$  (TYP) @ $I_D=0.5A, V_{GS}=4.5V$
  - $R_{DS(ON)}=0.46\ \Omega$  (TYP) @ $I_D=0.5A, V_{GS}=2.5V$
  - $R_{DS(ON)}=0.64\ \Omega$  (TYP) @ $I_D=0.3A, V_{GS}=1.8V$
- High speed switching.
- Small packing for easy mounting.

## APPLICATION

Inductive loads switching

## OUTLINE DRAWING

Unit: mm



TERMINAL CONNECTOR

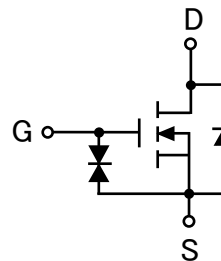
- ①: GATE
  - ②: SOURCE
  - ③: DRAIN
- JEITA: SC-59  
JEDEC: Similar to TO-236

## MAXIMUM RATINGS (Ta=25°C)

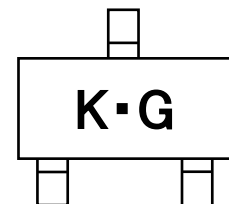
Parameter	Symbol	Rating	Unit
Drain-Source voltage	V <sub>DSS</sub>	20	V
Gate-Source voltage	V <sub>GS</sub>	±8	V
Drain current(DC)	I <sub>D</sub>	0.7	A
Drain current(Pulse)	I <sub>DP</sub>	1.4(※1)	A
Total power dissipation	P <sub>D</sub>	200	mW
Channel temperature	T <sub>ch</sub>	+150	°C
Storage temperature	T <sub>stg</sub>	-55~+150	°C

※1: Pw ≤ 10 μs, Duty cycle ≤ 1%

## EQUIVALENT CIRCUIT



## MARKING



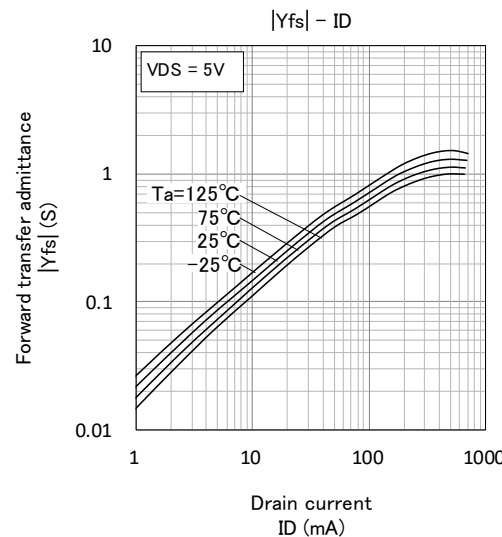
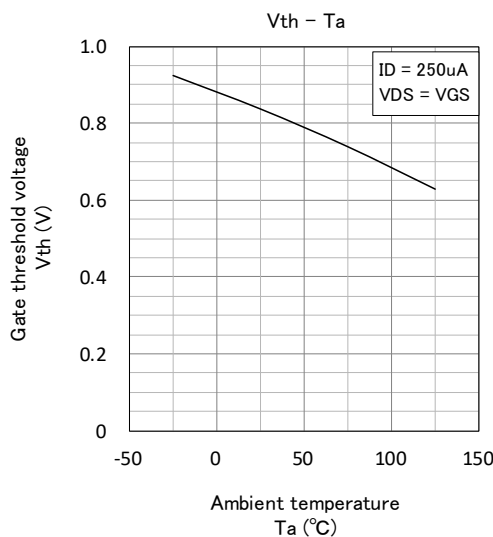
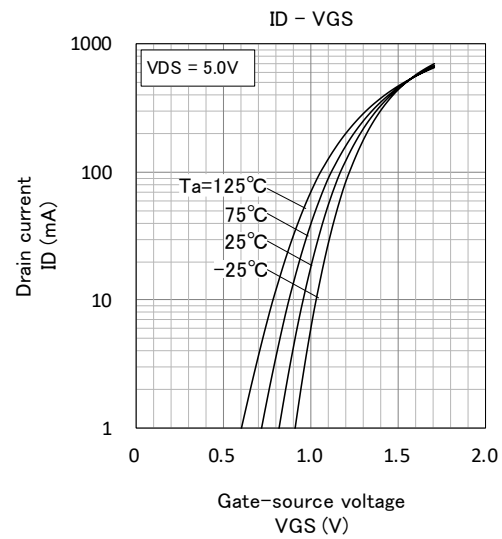
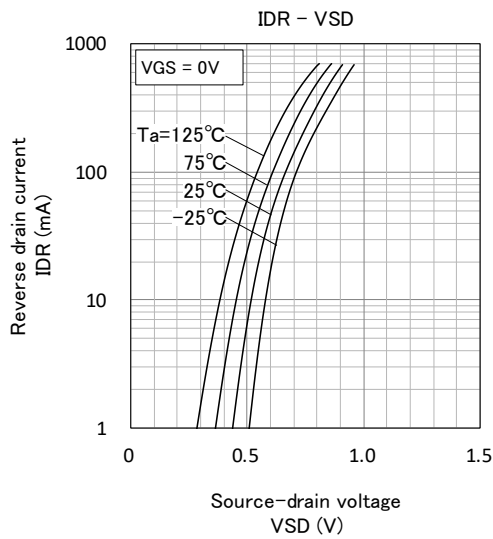
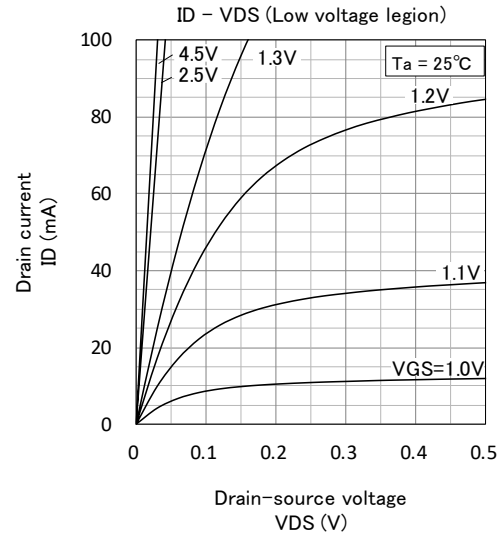
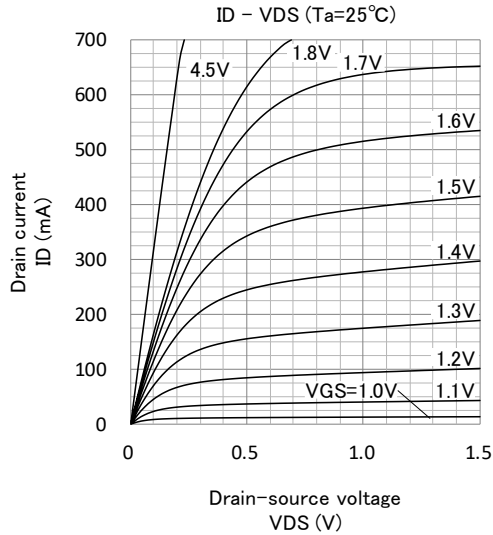
## ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> =100μA, V <sub>GS</sub> =0V	20	-	-	V
Gate-Source leak current	I <sub>GS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V	-	-	±10	μA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-	1	μA
Gate threshold voltage	V <sub>th</sub>	I <sub>D</sub> =250μA, V <sub>DS</sub> =V <sub>GS</sub>	0.5	-	1.0	V
Static Drain-Source on-state resistance	R <sub>DS(ON)</sub>	I <sub>D</sub> =0.5A, V <sub>GS</sub> =4.5V	-	0.33	-	Ω
		I <sub>D</sub> =0.5A, V <sub>GS</sub> =2.5V	-	0.46	-	
		I <sub>D</sub> =0.3A, V <sub>GS</sub> =1.8V	-	0.64	-	
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> =5V, V <sub>GS</sub> =0V, f=1MHz	-	64	-	pF
Output capacitance	C <sub>oss</sub>		-	16	-	
Switching time	t <sub>on</sub>	V <sub>DD</sub> =5V, I <sub>D</sub> =0.5A	-	22	-	ns
	t <sub>off</sub>	V <sub>GS</sub> =5V	-	30	-	

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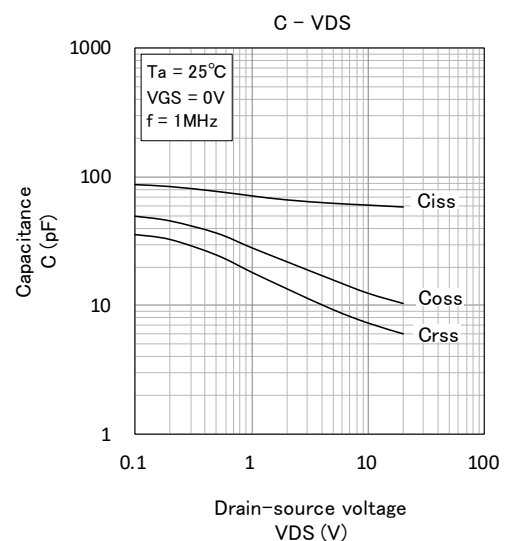
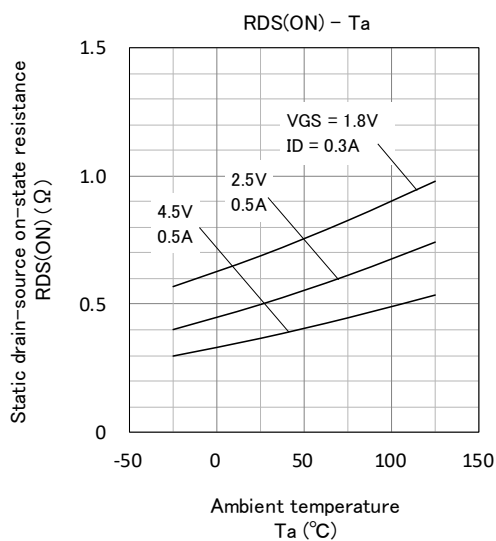
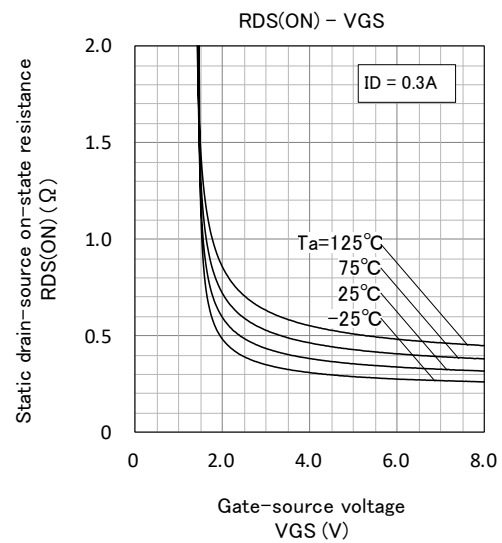
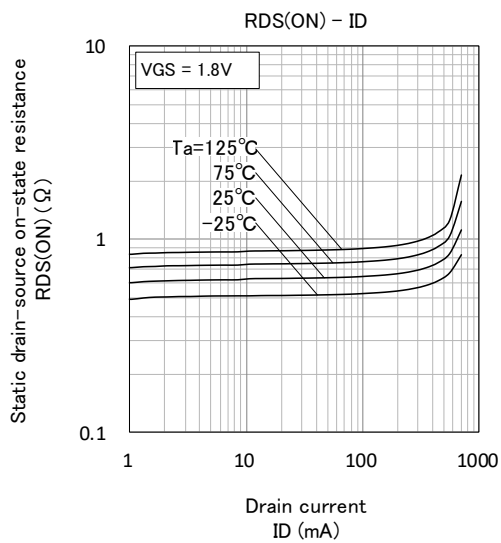
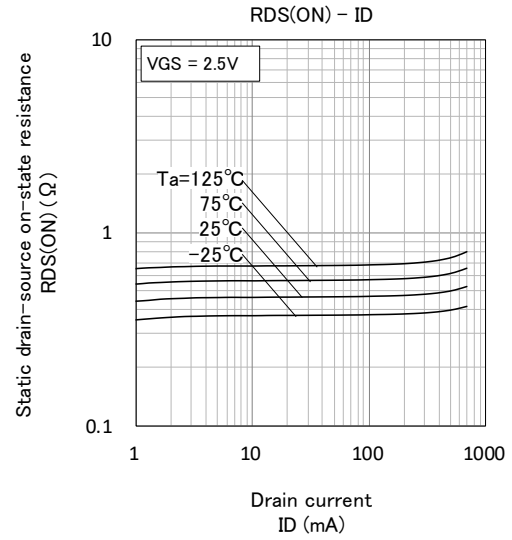
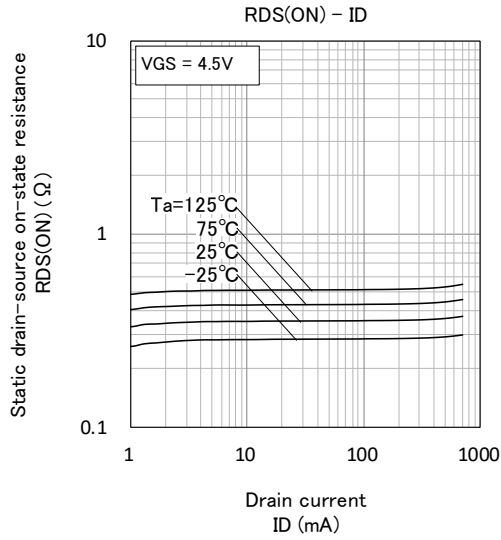
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## TYPICAL CHARACTERISTICS



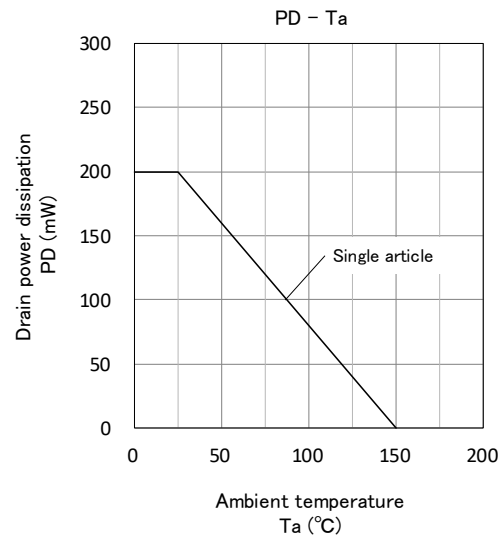
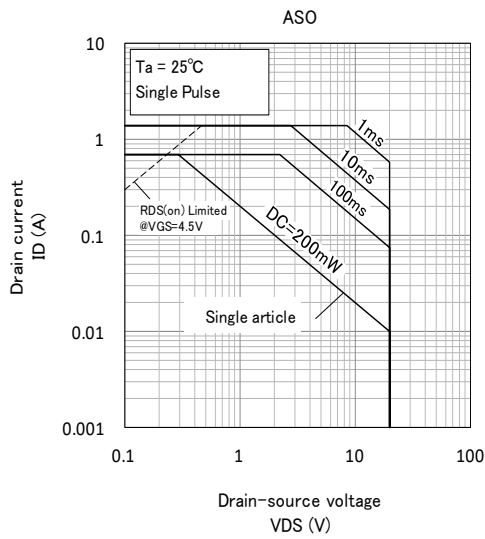
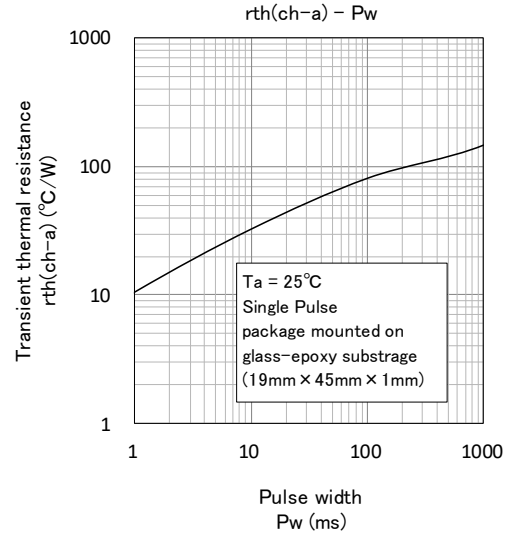
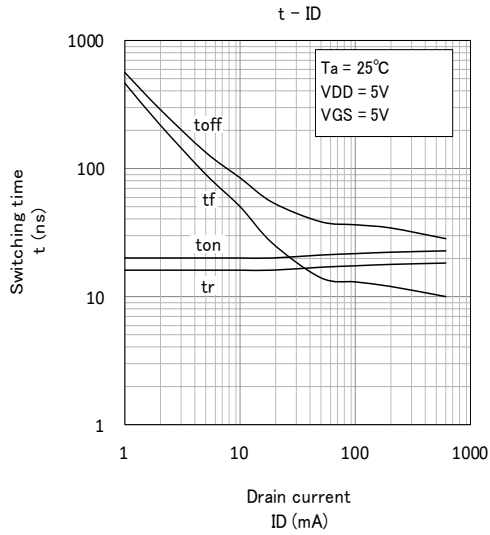
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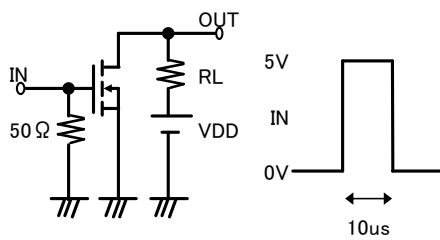


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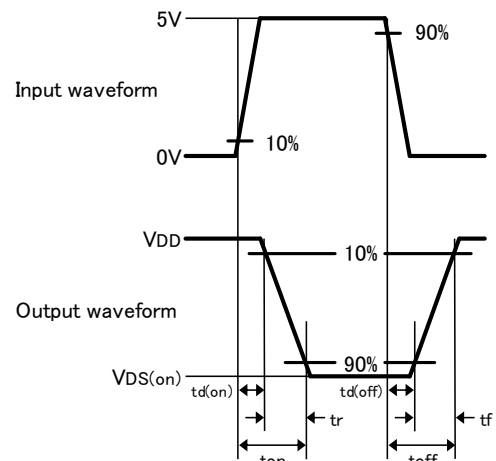
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## Switching time test condition



Duty  $\leq 1\%$   
Input:  $t_r, t_f < 10\text{ns}$   
 $V_{DD} = 5\text{V}$   
Common source  
 $T_a = 25^\circ\text{C}$



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